U.S. Application No.: 10/516,455

REMARKS

Status of the Application

Claims 1-4 are all the claims that have been examined in the application. Claims 1-4

stand rejected under 35 U.S.C. § 103(a) as being unpatentable over U.S. Patent 5,456,796 to

Gupta et al.

Claim Rejections - 35 U.S.C. § 103

Claims 1-4 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over U.S.

Patent 5,456,796 to Gupta et al.

Claim 1 recites, in part, "exciting the gas in the reaction chamber by a radiofrequency

excitation electromagnetic wave passing through a leakproof wall of dielectric material in order

to generate a plasma." The Examiner alleges that Gupta discloses all of the elements of claim 1.

Applicant respectfully disagrees.

Gupta discloses that an inert gas may be used to fill the reaction chamber during a plasma

ramp. When the plasma is at full power, reactants are introduced into the reaction chamber to

process a semiconductor wafer. See col. 3, lines 29-33. However, Gupta indicates that an RF

signal being slowly brought to full power is used to initiate the reaction. In Gupta, RF signal is

applied to electrodes within the reaction chamber, not by passing an RF wave through a

leakproof wall of dielectric material, as is recited in claim 1. Therefore, Gupta cannot disclose

all of the elements of claim 1, and claim 1 is patentable over the applied art.

Claims 2-4 are patentable at least by virtue of their dependency from claim 1.

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RESPONSE UNDER 37 C.F.R. § 1.116 Attorney Docket No.: Q84452

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Conclusion

In view of the above, reconsideration and allowance of this application are now believed

to be in order, and such actions are hereby solicited. If any points remain in issue which the

Examiner feels may be best resolved through a personal or telephone interview, the Examiner is

kindly requested to contact the undersigned at the telephone number listed below.

The USPTO is directed and authorized to charge all required fees, except for the Issue

Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any

overpayments to said Deposit Account.

Respectfully submitted,

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